

CLAIMS

1. A magnetic non-volatile memory device provided with a magnetic shielding structure for suppressing the influence of external magnetic fields, said device characterized by comprising:

a magnetic shield layer made from a soft magnetic metal on a surface of said device for suppressing penetration of magnetic flux into said device.

2. The magnetic non-volatile memory device according to claim 1, said device characterized in that:

said magnetic shield layers are formed on a device surface at the mounting side of said device, and on a device surface opposite to said mounting side of said device.

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3. The magnetic non-volatile memory device according to claim 1, said device characterized in that:

said magnetic shield layer is formed of a nano granular structure having a magnetic layer and a non-magnetic layer.

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4. The magnetic non-volatile memory device according to claim 1, said device characterized in that:

said magnetic shield layer has a composing element which is common to a part of an element of various layers composing said device.

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5. The magnetic non-volatile memory device according to claim 1, said device characterized in that:

a passivation film is formed on said magnetic shield layer.

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